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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	100
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	121-VFBGA, CSPBGA
Supplier Device Package	121-CSFBGA (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3lf-4300e-6mg121c

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Table 1-1. MachXO3L/LF Family Selection Guide

Features		MachXO3L-640/ MachXO3LF-640	MachXO3L-1300/ MachXO3LF-1300	MachXO3L-2100/ MachXO3LF-2100	MachXO3L-4300/ MachXO3LF-4300	MachXO3L-6900/ MachXO3LF-6900	MachXO3L-9400/ MachXO3LF-9400
LUTs		640	1300	2100	4300	6900	9400
Distributed RAM (kbits)		5	10	16	34	54	73
EBR SRAM (kbits)		64	64	74	92	240	432
Number of PLLs		1	1	1	2	2	2
Hardened Functions:	I^2C	2	2	2	2	2	2
	SPI	1	1	1	1	1	1
	Timer/Counter	1	1	1	1	1	1
	Oscillator	1	1	1	1	1	1
MIPI D-PHY Support		Yes	Yes	Yes	Yes	Yes	Yes
Multi Time Programmable NVCM		MachXO3L-640	MachXO3L-1300	MachXO3L-2100	MachXO3L-4300	MachXO3L-6900	MachXO3L-9400
Programmable Flash		MachXO3LF-640	MachXO3LF-1300	MachXO3LF-2100	MachXO3LF-4300	MachXO3LF-6900	MachXO3LF-9400
Packages				**IO**			
36-ball WLCSP[1] (2.5 mm x 2.5 mm, 0.4 mm)			28				
49-ball WLCSP[1] (3.2 mm x 3.2 mm, 0.4 mm)				38			
81-ball WLCSP[1] (3.8 mm x 3.8 mm, 0.4 mm)					63		
121-ball csfBGA[1] (6 mm x 6 mm, 0.5 mm)		100	100	100	100		
256-ball csfBGA[1] (9 mm x 9 mm, 0.5 mm)			206	206	206	206	206
324-ball csfBGA[1] (10 mm x 10 mm, 0.5 mm)				268	268	281	
256-ball caBGA[2] (14 mm x 14 mm, 0.8 mm)			206	206	206	206	206
324-ball caBGA[2] (15 mm x 15 mm, 0.8 mm)				279	279	279	
400-ball caBGA[2] (17 mm x 17 mm, 0.8 mm)					335	335	335
484-ball caBGA[2] (19 mm x 19 mm, 0.8 mm)							384

1. Package is only available for E=1.2 V devices.
2. Package is only available for C=2.5 V/3.3 V devices.

Introduction

MachXO3™ device family is an Ultra-Low Density family that supports the most advanced programmable bridging and IO expansion. It has the breakthrough IO density and the lowest cost per IO. The device IO features have the integrated support for latest industry standard IO.

The MachXO3L/LF family of low power, instant-on, non-volatile PLDs has five devices with densities ranging from 640 to 9400 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic these devices feature Embedded Block RAM (EBR), Distributed RAM, Phase Locked Loops (PLLs), pre-engineered source synchronous I/O support, advanced configuration support including dual-boot capability and hardened versions of commonly used functions such as SPI controller, I^2C controller and timer/counter. MachXO3LF devices also support User Flash Memory (UFM). These features allow these devices to be used in low cost, high volume consumer and system applications.

The MachXO3L/LF devices are designed on a 65nm non-volatile low power process. The device architecture has several features such as programmable low swing differential I/Os and the ability to turn off I/O banks, on-chip PLLs and oscillators dynamically. These features help manage static and dynamic power consumption resulting in low static power for all members of the family.

The MachXO3L/LF devices are available in two versions C and E with two speed grades: -5 and -6, with -6 being the fastest. C devices have an internal linear voltage regulator which supports external VCC supply voltages of 3.3 V or 2.5 V. E devices only accept 1.2 V as the external VCC supply voltage. With the exception of power supply voltage both C and E are functionally compatible with each other.

The MachXO3L/LF PLDs are available in a broad range of advanced halogen-free packages ranging from the space saving 2.5 x 2.5 mm WLCSP to the 19 x 19 mm caBGA. MachXO3L/LF devices support density migration within the same package. Table 1-1 shows the LUT densities, package and I/O options, along with other key parameters.

The MachXO3L/LF devices offer enhanced I/O features such as drive strength control, slew rate control, PCI compatibility, bus-keeper latches, pull-up resistors, pull-down resistors, open drain outputs and hot socketing. Pull-up, pull-down and bus-keeper features are controllable on a “per-pin” basis.

A user-programmable internal oscillator is included in MachXO3L/LF devices. The clock output from this oscillator may be divided by the timer/counter for use as clock input in functions such as LED control, key-board scanner and similar state machines.

The MachXO3L/LF devices also provide flexible, reliable and secure configuration from on-chip NVCM/Flash. These devices can also configure themselves from external SPI Flash or be configured by an external master through the JTAG test access port or through the I^{2}C port. Additionally, MachXO3L/LF devices support dual-boot capability (using external Flash memory) and remote field upgrade (TransFR) capability.

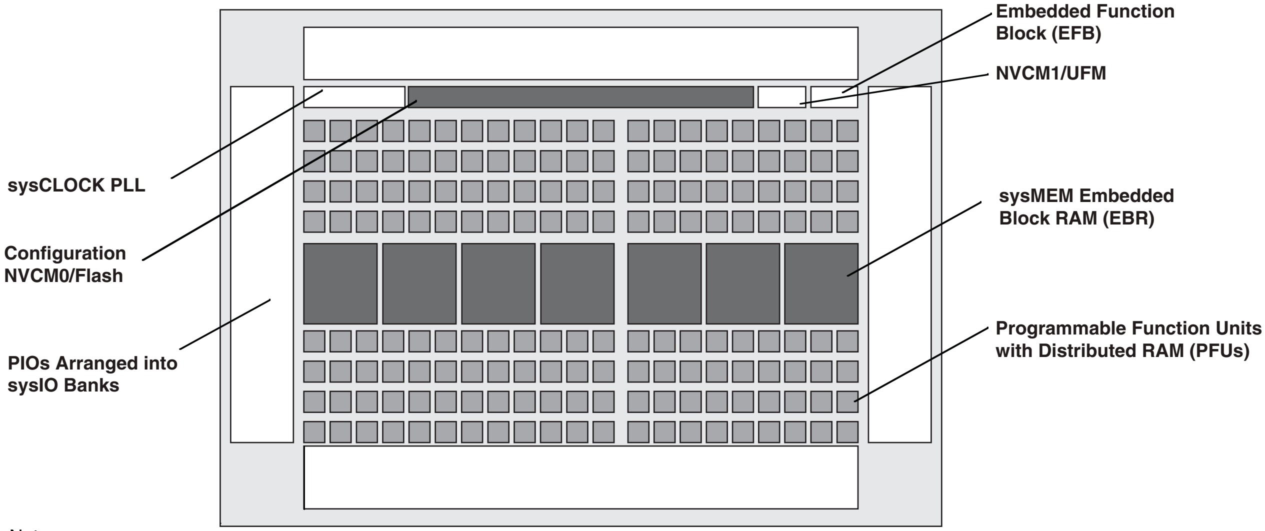
Lattice provides a variety of design tools that allow complex designs to be efficiently implemented using the MachXO3L/LF family of devices. Popular logic synthesis tools provide synthesis library support for MachXO3L/LF. Lattice design tools use the synthesis tool output along with the user-specified preferences and constraints to place and route the design in the MachXO3L/LF device. These tools extract the timing from the routing and back-annotate it into the design for timing verification.

Lattice provides many pre-engineered IP (Intellectual Property) LatticeCORE™ modules, including a number of reference designs licensed free of charge, optimized for the MachXO3L/LF PLD family. By using these configurable soft core IP cores as standardized blocks, users are free to concentrate on the unique aspects of their design, increasing their productivity.

Architecture Overview

The MachXO3L/LF family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). All logic density devices in this family have sysCLOCK™ PLLs and blocks of sysMEM Embedded Block RAM (EBRs). Figure 2-1 and Figure 2-2 show the block diagrams of the various family members.

Figure 2-1. Top View of the MachXO3L/LF-1300 Device



Notes:
- MachXO3L/LF-640 is similar to MachXO3L/LF-1300. MachXO3L/LF-640 has a lower LUT count.
- MachXO3L devices have NVCM, MachXO3LF devices have Flash.

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Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the NVCM or Configuration Flash.

MachXO3LF EBR initialization data can also be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO3LF devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

Table 2-6. EBR Signal Descriptions

Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE[1]	Output Clock Enable	Active High
RST	Reset	Active High
BE[1]	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	—
DI	Data In	—
DO	Data Out	—
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	—
FF	FIFO RAM Full Flag	—
AEF	FIFO RAM Almost Empty Flag	—
EF	FIFO RAM Empty Flag	—
RPRST	FIFO RAM Read Pointer Reset	—

1. Optional signals.
2. For dual port EBR primitives a trailing 'A' or 'B' in the signal name specifies the EBR port A or port B respectively.
3. For FIFO RAM mode primitive, a trailing 'R' or 'W' in the signal name specifies the FIFO read port or write port respectively.
4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).
5. In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port chip select, ORE is the output read enable.

The EBR memory supports three forms of write behavior for single or dual port operation:

1. **Normal** – Data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
2. **Write Through** – A copy of the input data appears at the output of the same port. This mode is supported for all data widths.
3. **Read-Before-Write** – When new data is being written, the old contents of the address appears at the output.

FIFO Configuration

The FIFO has a write port with data-in, CEW, WE and CLKW signals. There is a separate read port with data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. Table 2-7 shows the range of programming values for these flags.

Table 2-7. Programmable FIFO Flag Ranges

Flag Name	Programming Range
Full (FF)	1 to max (up to 2^N-1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

N = Address bit width.

The FIFO state machine supports two types of reset signals: RST and RPRST. The RST signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device wake up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-10. The reset timing rules apply to the RPReset input versus the RE input and the RST input versus the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs. For more details refer to TN1290, Memory Usage Guide for MachXO3 Devices.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO3L/LF devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO3L/LF devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

All PIO pairs can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these devices have on-chip differential termination and also provide PCI support.

Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysIO buffers.

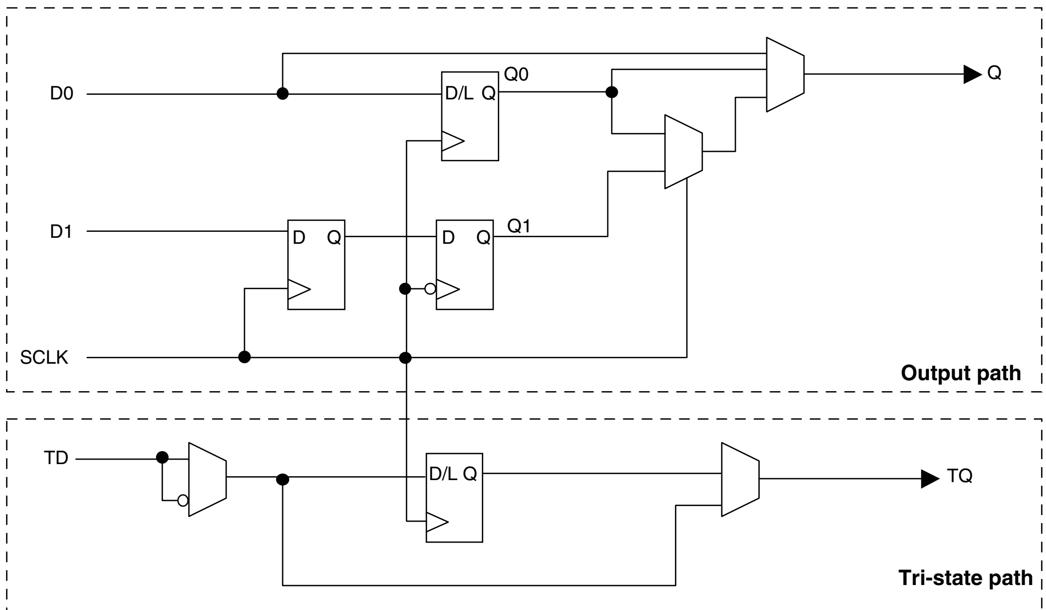
Left, Top, Bottom Edges

In SDR mode, D0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a D-type register or latch.

In DDR generic mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the same clock is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-12 shows the output register block on the left, top and bottom edges.

Figure 2-12. MachXO3L/LF Output Register Block Diagram (PIO on the Left, Top and Bottom Edges)



Tri-state Register Block

The tri-state register block registers tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation. In SDR, TD input feeds one of the flip-flops that then feeds the output.

Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDRX4 (8:1) gearbox or as two ODDRX2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDRX4(8:1): D[7:0]		
GDDRX2(4:1)(IOL-A): D[3:0]		
GDDRX2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-14 shows the output gearbox block diagram.

Table 2-12. Supported Output Standards

Output Standard	V_{CCIO} (Typ.)
Single-Ended Interfaces	
LVTTL	3.3
LVCMOS33	3.3
LVCMOS25	2.5
LVCMOS18	1.8
LVCMOS15	1.5
LVCMOS12	1.2
LVCMOS33, Open Drain	—
LVCMOS25, Open Drain	—
LVCMOS18, Open Drain	—
LVCMOS15, Open Drain	—
LVCMOS12, Open Drain	—
PCI33	3.3
Differential Interfaces	
LVDS[1]	2.5, 3.3
BLVDS, MLVDS, RSDS [1]	2.5
LVPECL[1]	3.3
MIPI[1]	2.5
LVTTLD	3.3
LVCMOS33D	3.3
LVCMOS25D	2.5
LVCMOS18D	1.8

1. These interfaces can be emulated with external resistors in all devices.

sysIO Buffer Banks

The numbers of banks vary between the devices of this family. MachXO3L/LF-1300 in the 256 Ball packages and the MachXO3L/LF-2100 and higher density devices have six I/O banks (one bank on the top, right and bottom side and three banks on the left side). The MachXO3L/LF-1300 and lower density devices have four banks (one bank per side). Figures 2-15 and 2-16 show the sysIO banks and their associated supplies for all devices.

Hardened Timer/Counter

MachXO3L/LF devices provide a hard Timer/Counter IP core. This Timer/Counter is a general purpose, bi-directional, 16-bit timer/counter module with independent output compare units and PWM support. The Timer/Counter supports the following functions:

- Supports the following modes of operation:
  — Watchdog timer
  — Clear timer on compare match
  — Fast PWM
  — Phase and Frequency Correct PWM
- Programmable clock input source
- Programmable input clock prescaler
- One static interrupt output to routing
- One wake-up interrupt to on-chip standby mode controller.
- Three independent interrupt sources: overflow, output compare match, and input capture
- Auto reload
- Time-stamping support on the input capture unit
- Waveform generation on the output
- Glitch-free PWM waveform generation with variable PWM period
- Internal WISHBONE bus access to the control and status registers
- Stand-alone mode with preloaded control registers and direct reset input

Figure 2-20. Timer/Counter Block Diagram

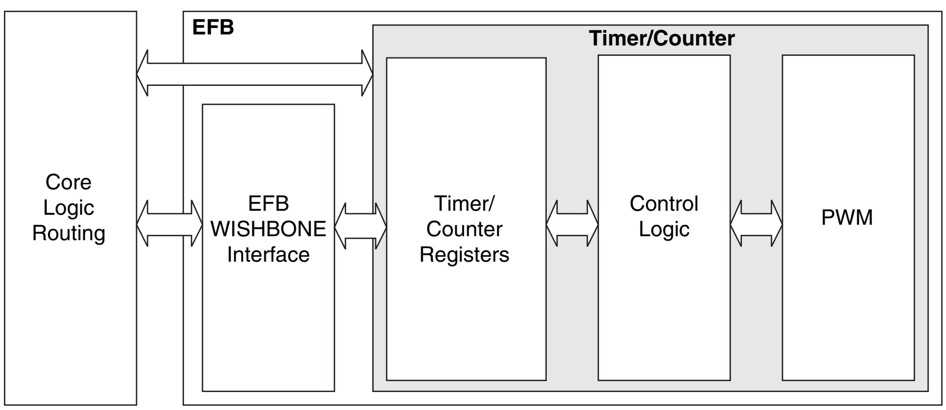


Table 2-16. Timer/Counter Signal Description

Port	I/O	Description
tc_clki	I	Timer/Counter input clock signal
tc_rstn	I	Register tc_rstn_ena is preloaded by configuration to always keep this pin enabled
tc_ic	I	Input capture trigger event, applicable for non-pwm modes with WISHBONE interface. If enabled, a rising edge of this signal will be detected and synchronized to capture tc_cnt value into tc_icr for time-stamping.
tc_int	O	Without WISHBONE – Can be used as overflow flag With WISHBONE – Controlled by three IRQ registers
tc_oc	O	Timer counter output signal

Security and One-Time Programmable Mode (OTP)

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM-based FPGAs. This is further enhanced by device locking. MachXO3L/LF devices contain security bits that, when set, prevent the readback of the SRAM configuration and NVCM/Flash spaces. The device can be in one of two modes:

1. Unlocked – Readback of the SRAM configuration and NVCM/Flash spaces is allowed.
2. Permanently Locked – The device is permanently locked.

Once set, the only way to clear the security bits is to erase the device. To further complement the security of the device, a One Time Programmable (OTP) mode is available. Once the device is set in this mode it is not possible to erase or re-program the NVCM/Flash and SRAM OTP portions of the device. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

Password

The MachXO3LF supports a password-based security access feature also known as Flash Protect Key. Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. The Flash Protect Key feature provides a method of controlling access to the Configuration and Programming modes of the device. When enabled, the Configuration and Programming edit mode operations (including Write, Verify and Erase operations) are allowed only when coupled with a Flash Protect Key which matches that expected by the device. Without a valid Flash Protect Key, the user can perform only rudimentary non-configuration operations such as Read Device ID. For more details, refer to TN1313, Using Password Security with MachXO3 Devices.

Dual Boot

MachXO3L/LF devices can optionally boot from two patterns, a primary bitstream and a golden bitstream. If the primary bitstream is found to be corrupt while being downloaded into the SRAM, the device shall then automatically re-boot from the golden bitstream. Note that the primary bitstream must reside in the external SPI Flash. The golden image MUST reside in an on-chip NVCM/Flash. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

Soft Error Detection

The SED feature is a CRC check of the SRAM cells after the device is configured. This check ensures that the SRAM cells were configured successfully. This feature is enabled by a configuration bit option. The Soft Error Detection can also be initiated in user mode via an input to the fabric. The clock for the Soft Error Detection circuit is generated using a dedicated divider. The undivided clock from the on-chip oscillator is the input to this divider. For low power applications users can switch off the Soft Error Detection circuit. For more details, refer to TN1292, MachXO3 Soft Error Detection Usage Guide.

Soft Error Correction

The MachXO3LF device supports Soft Error Correction (SEC). Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. When BACKGROUND_RECONFIG is enabled using the Lattice Diamond Software in a design, asserting the PROGRAMN pin or issuing the REFRESH sysConfig command refreshes the SRAM array from configuration memory. Only the detected error bit is corrected. No other SRAM cells are changed, allowing the user design to function uninterrupted.

During the project design phase, if the overall system cannot guarantee containment of the error or its subsequent effects on downstream data or control paths, Lattice recommends using SED only. The MachXO3 can be then be soft-reset by asserting PROGRAMN or issuing the Refresh command over a sysConfig port in response to SED. Soft-reset additionally erases the SRAM array prior to the SRAM refresh, and asserts internal Reset circuitry to guarantee a known state. For more details, refer to TN1292, MachXO3 Soft Error Detection (SED)/Correction (SEC) Usage Guide.

Power-On-Reset Voltage Levels[1, 2, 3, 4, 5]

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for C devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	µA

1. Insensitive to sequence of V_{CC} and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO}.
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

ESD Performance

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.

MIPI D-PHY Emulation

MachXO3L/LF devices can support MIPI D-PHY unidirectional HS (High Speed) and bidirectional LP (Low Power) inputs and outputs via emulation. In conjunction with external resistors High Speed IOs use the LVDS25E buffer and Low Power IOs use the LVCMOS buffers. The scheme shown in Figure 3-4 is one possible solution for MIPI D-PHY Receiver implementation. The scheme shown in Figure 3-5 is one possible solution for MIPI D-PHY Transmitter implementation.

Figure 3-4. MIPI D-PHY Input Using External Resistors

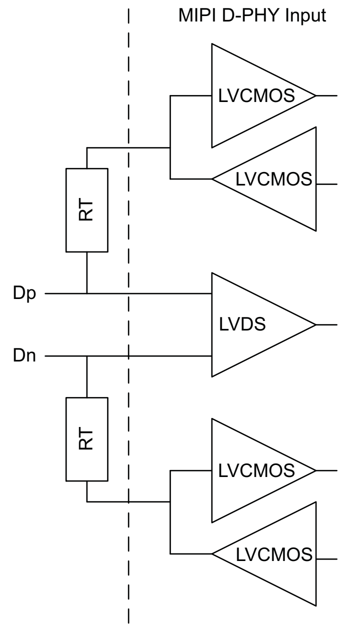


Table 3-4. MIPI DC Conditions[1]

	Description	Min.	Typ.	Max.	Units
Receiver					
External Termination					
RT	1% external resistor with VCCIO=2.5 V	—	50	—	Ohms
	1% external resistor with VCCIO=3.3 V	—	50	—	Ohms
High Speed					
VCCIO	VCCIO of the Bank with LVDS Emulated input buffer	—	2.5	—	V
	VCCIO of the Bank with LVDS Emulated input buffer	—	3.3	—	V
VCMRX	Common-mode voltage HS receive mode	150	200	250	mV
VIDTH	Differential input high threshold	—	—	100	mV
VIDTL	Differential input low threshold	–100	—	—	mV
VIHHS	Single-ended input high voltage	—	—	300	mV
VILHS	Single-ended input low voltage	100	—	—	mV
ZID	Differential input impedance	80	100	120	Ohms

Table 3-5. MIPI D-PHY Output DC Conditions[1]

	Description	Min.	Typ.	Max.	Units
Transmitter					
External Termination					
RL	1% external resistor with VCCIO = 2.5 V	—	50	—	Ohms
	1% external resistor with VCCIO = 3.3 V	—	50	—	
RH	1% external resistor with performance up to 800 Mbps or with performance up 900 Mbps when VCCIO = 2.5 V	—	330	—	Ohms
	1% external resistor with performance between 800 Mbps to 900 Mbps when VCCIO = 3.3 V	—	464	—	Ohms
High Speed					
VCCIO	VCCIO of the Bank with LVDS Emulated output buffer	—	2.5	—	V
	VCCIO of the Bank with LVDS Emulated output buffer	—	3.3	—	V
VCMTX	HS transmit static common mode voltage	150	200	250	mV
VOD	HS transmit differential voltage	140	200	270	mV
VOHHS	HS output high voltage	—	—	360	V
ZOS	Single ended output impedance	—	50	—	Ohms
ΔZOS	Single ended output impedance mismatch	—	—	10	%
Low Power					
VCCIO	VCCIO of the Bank with LVCMOS12D 6 mA drive bidirectional IO buffer	—	1.2	—	V
VOH	Output high level	1.1	1.2	1.3	V
VOL	Output low level	–50	0	50	mV
ZOLP	Output impedance of LP transmitter	110	—	—	Ohms

1. Over Recommended Operating Conditions

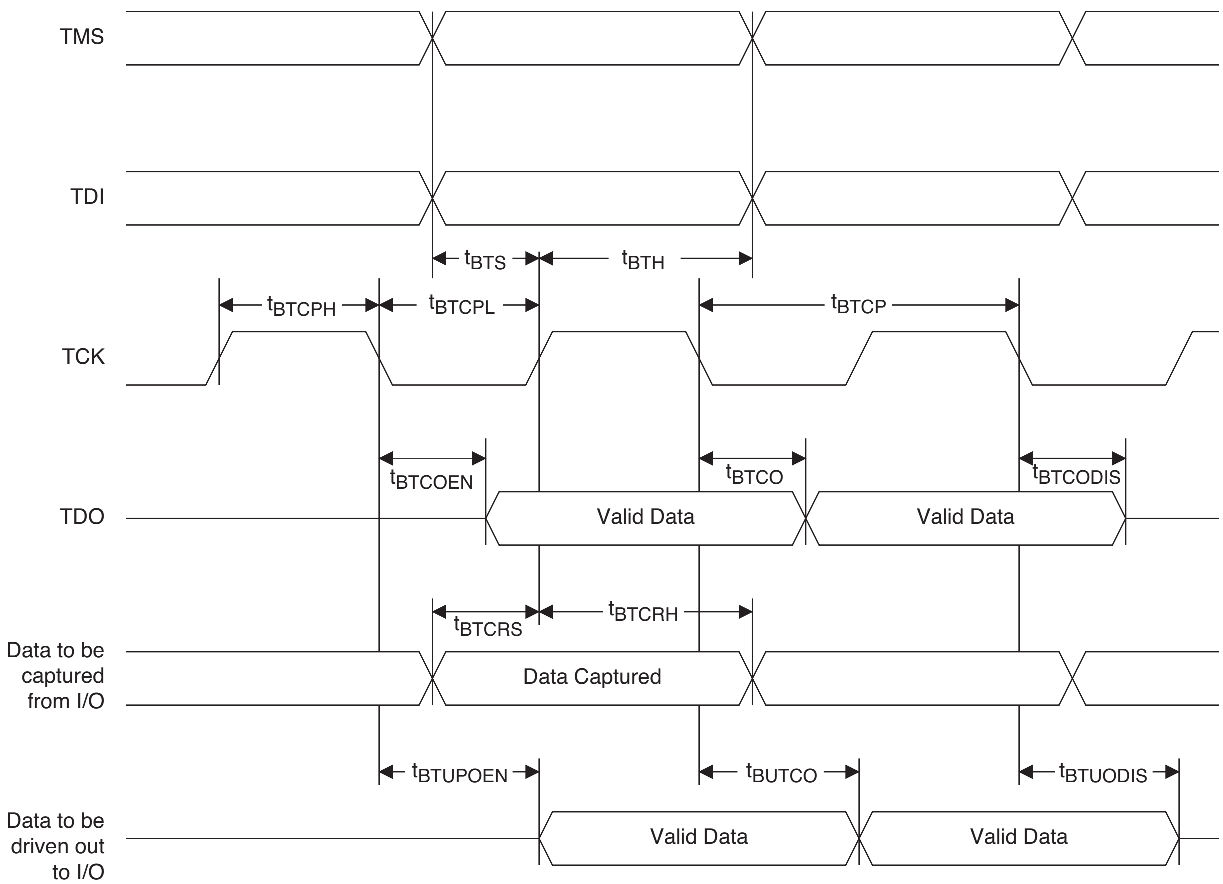
Parameter	Description	Device	–6 Min.	–6 Max.	–5 Min.	–5 Max.	Units
Generic DDRX4 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_TX.ECLK.Centered[8, 9]							
t_{DVB}	Output Data Valid Before CLK Output	MachXO3L/LF devices, top side only	0.455	—	0.570	—	ns
t_{DVA}	Output Data Valid After CLK Output		0.455	—	0.570	—	ns
f_{DATA}	DDRX4 Serial Output Data Speed		—	800	—	630	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency (minimum limited by PLL)		—	400	—	315	MHz
f_{SCLK}	SCLK Frequency		—	100	—	79	MHz
7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1[8, 9]							
t_{DIB}	Output Data Invalid Before CLK Output	MachXO3L/LF devices, top side only	—	0.160	—	0.180	ns
t_{DIA}	Output Data Invalid After CLK Output		—	0.160	—	0.180	ns
f_{DATA}	DDR71 Serial Output Data Speed		—	756	—	630	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	378	—	315	MHz
f_{CLKOUT}	7:1 Output Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	MHz
MIPI D-PHY Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input - GDDRX4_TX.ECLK.Centered[10, 11, 12]							
t_{DVB}	Output Data Valid Before CLK Output	All MachXO3L/LF devices, top side only	0.200	—	0.200	—	UI
t_{DVA}	Output Data Valid After CLK Output		0.200	—	0.200	—	UI
f_{DATA}[14]	MIPI D-PHY Output Data Speed		—	900	—	900	Mbps
f_{DDRX4}[14]	MIPI D-PHY ECLK Frequency (minimum limited by PLL)		—	450	—	450	MHz
f_{SCLK}[14]	SCLK Frequency		—	112.5	—	112.5	MHz

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
5. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\text{ ns})/2$.
6. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (–6), 113 ps (–5), 120 ps (–4).
7. This number for general purpose usage. Duty cycle tolerance is +/–10%.
8. Duty cycle is +/– 5% for system usage.
9. Performance is calculated with 0.225 UI.
10. Performance is calculated with 0.20 UI.
11. Performance for Industrial devices are only supported with VCC between 1.16 V to 1.24 V.
12. Performance for Industrial devices and –5 devices are not modeled in the Diamond design tool.
13. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
14. Above 800 Mbps is only supported with WLCSP and csfBGA packages
15. Between 800 Mbps to 900 Mbps:
    a. VIDTH exceeds the MIPI D-PHY Input DC Conditions Table 3-4 and can be calculated with the equation tSU or tH = -0.0005*VIDTH + 0.3284
    b. Example calculations
        i. tSU and tHO = 0.28 with VIDTH = 100 mV
        ii. tSU and tHO = 0.25 with VIDTH = 170 mV
        iii. tSU and tHO = 0.20 with VIDTH = 270 mV

JTAG Port Timing Specifications

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	20	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

Figure 3-8. JTAG Port Timing Waveforms



sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t_{PRGM}	PROGRAMN low pulse accept		55	—	ns
t_{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t_{INITL}	INITN low time	LCMXO3L/LF-640/ LCMXO3L/LF-1300	—	55	us
		LCMXO3L/LF-1300 256-Ball Package/ LCMXO3L/LF-2100	—	70	us
		LCMXO3L/LF-2100 324-Ball Package/ LCMXO3-4300	—	105	us
		LCMXO3L/LF-4300 400-Ball Package/ LCMXO3-6900	—	130	us
		LCMXO3L/LF-9400C	—	175	us
$t_{DPPINIT}$	PROGRAMN low to INITN low		—	150	ns
$t_{DPPDONE}$	PROGRAMN low to DONE low		—	150	ns
t_{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f_{MAX}	CCLK clock frequency		—	66	MHz
t_{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t_{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t_{STSU}	CCLK setup time		2	—	ns
t_{STH}	CCLK hold time		0	—	ns
t_{STCO}	CCLK falling edge to valid output		—	10	ns
t_{STOZ}	CCLK falling edge to valid disable		—	10	ns
t_{STOV}	CCLK falling edge to valid enable		—	10	ns
t_{SCS}	Chip select high time		25	—	ns
t_{SCSS}	Chip select setup time		3	—	ns
t_{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f_{MAX}	MCLK clock frequency		—	133	MHz
t_{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t_{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t_{STSU}	MCLK setup time		5	—	ns
t_{STH}	MCLK hold time		1	—	ns
t_{CSSPI}	INITN high to chip select low		100	200	ns
t_{MCLK}	INITN high to first MCLK edge		0.75	1	us

Signal Descriptions (Cont.)

Signal Name	I/O	Descriptions
Configuration (Dual function pins used during sysCONFIG)		
PROGRAMN	I	Initiates configuration sequence when asserted low. This pin always has an active pull-up.
INITN	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, a pull-up is enabled.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the start-up sequence is in progress.
MCLK/CCLK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI mode. Output Configuration Clock for configuring an FPGA in SPI and SPIm configuration modes.
SN	I	Slave SPI active low chip select input.
CSSPIN	I/O	Master SPI active low chip select output.
SI/SPISI	I/O	Slave SPI serial data input and master SPI serial data output.
SO/SPISO	I/O	Slave SPI serial data output and master SPI serial data input.
SCL	I/O	Slave I^2C clock input and master I^2C clock output.
SDA	I/O	Slave I^2C data input and master I^2C data output.

	MachXO3L/LF-2100					
	WLCSP49	CSFBGA121	CSFBGA256	CSFBGA324	CABGA256	CABGA324
General Purpose IO per Bank						
Bank 0	19	24	50	71	50	71
Bank 1	0	26	52	62	52	68
Bank 2	13	26	52	72	52	72
Bank 3	0	7	16	22	16	24
Bank 4	0	7	16	14	16	16
Bank 5	6	10	20	27	20	28
Total General Purpose Single Ended IO	38	100	206	268	206	279
Differential IO per Bank						
Bank 0	10	12	25	36	25	36
Bank 1	0	13	26	30	26	34
Bank 2	6	13	26	36	26	36
Bank 3	0	3	8	10	8	12
Bank 4	0	3	8	6	8	8
Bank 5	3	5	10	13	10	14
Total General Purpose Differential IO	19	49	103	131	103	140
Dual Function IO	25	33	33	37	33	37
Number 7:1 or 8:1 Gearboxes						
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	7	14	18	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	13	14	18	14	18
High-speed Differential Outputs						
Bank 0	5	7	14	18	14	18
VCCIO Pins						
Bank 0	2	1	4	4	4	4
Bank 1	0	1	3	4	4	4
Bank 2	1	1	4	4	4	4
Bank 3	0	1	2	2	1	2
Bank 4	0	1	2	2	2	2
Bank 5	1	1	2	2	1	2
VCC	2	4	8	8	8	10
GND	4	10	24	16	24	16
NC	0	0	0	13	1	0
Reserved for Configuration	1	1	1	1	1	1
Total Count of Bonded Pins	**49**	**121**	**256**	**324**	**256**	**324**

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-6900E-5MG256C	6900	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-6900E-6MG256C	6900	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-6900E-5MG256I	6900	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-6900E-6MG256I	6900	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-6900E-5MG324C	6900	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3LF-6900E-6MG324C	6900	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3LF-6900E-5MG324I	6900	1.2 V	5	Halogen-Free csfBGA	324	IND
LCMXO3LF-6900E-6MG324I	6900	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3LF-6900C-5BG256C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-6900C-6BG256C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-6900C-5BG256I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-6900C-6BG256I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3LF-6900C-5BG324C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3LF-6900C-6BG324C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3LF-6900C-5BG324I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3LF-6900C-6BG324I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
LCMXO3LF-6900C-5BG400C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3LF-6900C-6BG400C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3LF-6900C-5BG400I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3LF-6900C-6BG400I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-9400E-5MG256C	9400	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-9400E-6MG256C	9400	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-9400E-5MG256I	9400	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-9400E-6MG256I	9400	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-9400C-5BG256C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-9400C-6BG256C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-9400C-5BG256I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-9400C-6BG256I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3LF-9400C-5BG400C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3LF-9400C-6BG400C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3LF-9400C-5BG400I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3LF-9400C-6BG400I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	400	IND
LCMXO3LF-9400C-5BG484C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	484	COM
LCMXO3LF-9400C-6BG484C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	484	COM
LCMXO3LF-9400C-5BG484I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	484	IND
LCMXO3LF-9400C-6BG484I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	484	IND